

# YJ Planar Schottky Barrier Diode Die Specification

60V 10A, 88mil, Schottky barrier diode die based on silicon planar process

Part No.: PSB088M060SS-280A

## Main Products Characteristics

~ A<sub>F</sub> = 10 A

~ Max. T<sub>b</sub> = 150 °C

~ ESD: >8KV, IEC61000-4-2 (Class B)

~ T<sub>stg</sub>: A\*

## Maximum Ratings

## Static Electrical Characteristics (T<sub>a</sub> = 25°C)

I<sub>F</sub> = 10 A

P<sub>tot</sub> = 300 mW, 2%

## Device Schematics and Outline Drawing

Die Thickness \*

Die Size \*\*

Top Metal Pad

Active Area

Top Metal

Back Metal

Note: 1 \*: Also can offer device with 8 mils thickness

2 \*\*: Cutting street width is around 1.5 mils

## Important Notice